

NPN SILICON RF TRANSISTOR

DESCRIPTION:

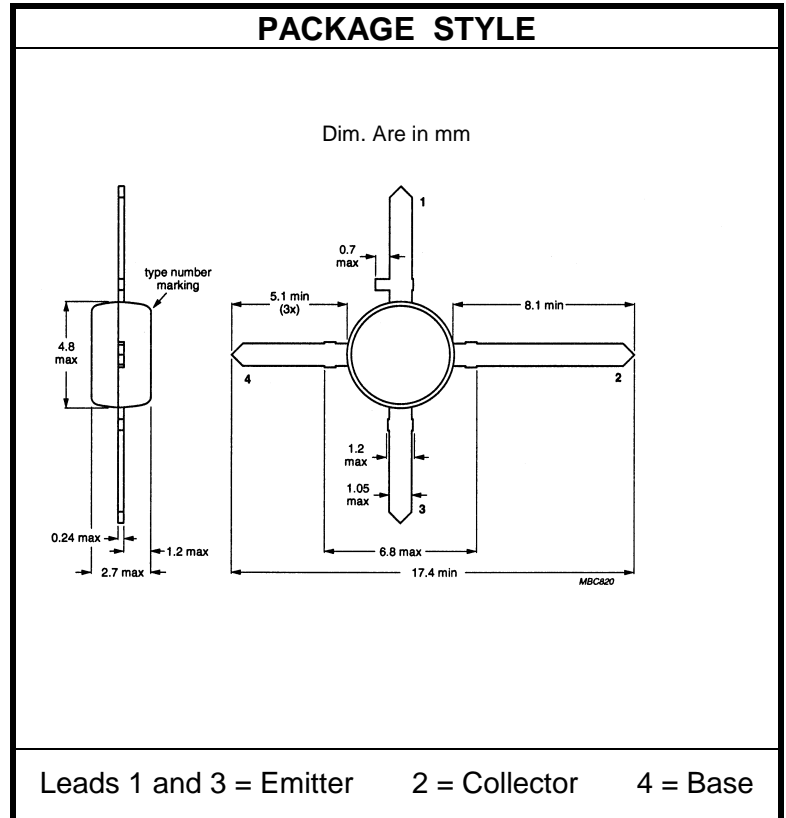
The **ASI MRF581A** is Designed for High current low Power Amplifier Applications up to 1.0 GHz.

FEATURES:

- Low Noise Figure
- Low Intermodulation Distortion
- High Gain
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	200 mA
V_{CBO}	30 V
V_{CEO}	15 V
V_{EBO}	2.5 V
P_{DISS}	1.25 W @ $T_C = 25^\circ C$
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0 \text{ mA}$		30			V
BV_{CEO}	$I_C = 5.0 \text{ mA}$		15			V
BV_{EBO}	$I_E = 100 \mu A$		2.5			V
I_{EBO}	$V_{EB} = 2.0 \text{ V}$				100	μA
I_{CBO}	$V_{CB} = 15 \text{ V}$				100	μA
h_{FE}	$V_{CE} = 5.0 \text{ V}$	$I_C = 50 \text{ mA}$	90		250	---
C_{cb}	$V_{CB} = 10 \text{ V}$	$f = 1.0 \text{ MHz}$		2.0	3.0	pF
G_P	$V_{CC} = 10 \text{ V}$	$I_C = 50$	13	15.5		dB